

(11) Publication number:

63003414 A

Generated Document.

## PATENT ABSTRACTS OF JAPAN

(21) Application number: 61147380

(51) Intl. Cl.: H01L 21/205

(22) Application date: **24.06.86** 

(30) Priority:

08.01.88

(43) Date of application

publication:

(84) Designated contracting

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## SILICON FILM (54) MANUFACTURE OF

(57) Abstract:

characteristics by a method wherein a deposition rate and excellent electric silicon film having a sufficient PURPOSE: To form an amorphous

thermal CVD method is performed at the substrate temperature of 480°C or below using trisilane or higher silanes.

gas blow- out hole 5, the exhaust hole of a heating means 2, a susceptor 3, a consisting of a wafer and the like is of the substrate 4 by thermal silicon film is formed on the surface chamber 1. As a result, an amorphous silane of high order which is higher exhaust means 7, they are placed on and the like connected to a gas inserted into the chamber 1 consisting chamber 1 in advance, and after the atmospheric gas is introduced into the decomposition reaction. At this time, than trisilane is introduced into the the upper surface of the susceptor 3. CONSTITUTION: The substrate 4 substantially by performing a thermal and the temperature variation when a been stabilized, raw gas is introduced, temperature of the substrate 4 has thereabout by a heating means 2, the When they are heated up to 400°C or film is formed can be made small

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